2N3903 is a Preferred Device

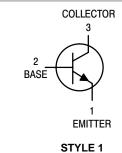
# **General Purpose Transistors**

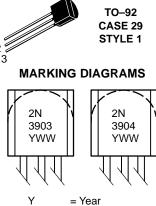
**NPN Silicon** 



## ON Semiconductor\*\*

#### http://onsemi.com





WW = Work Week

#### **ORDERING INFORMATION**

Device	Package	Shipping
2N3903	TO-92	5000 Units/Box
2N3903RLRM	TO-92	2000/Ammo Pack
2N3904	TO-92	5000 Units/Box
2N3904RLRA	TO-92	2000/Tape & Reel
2N3904RLRE	TO-92	2000/Tape & Reel
2N3904RLRM	TO-92	2000/Ammo Pack
2N3904RLRP	TO-92	2000/Ammo Pack
2N3904RL1	TO-92	2000/Tape & Reel
2N3904ZL1	TO-92	2000/Ammo Pack

**Preferred** devices are recommended choices for future use and best overall value.

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	40	Vdc
Collector–Base Voltage	VCBO	60	Vdc
Emitter-Base Voltage	VEBO	6.0	Vdc
Collector Current – Continuous	IC	200	mAdc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	PD	625 5.0	mW mW/°C
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	TJ, Tstg	–55 to +150	°C

#### THERMAL CHARACTERISTICS (Note 1.)

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	200	°C/W
Thermal Resistance, Junction to Case	R <sub>θ</sub> JC	83.3	°C/W

1. Indicates Data in addition to JEDEC Requirements.

## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Breakdown Voltage (Note 2.) ( $I_C = 1.0 \text{ mAdc}, I_B = 0$ )	V(BR)CEO	40	-	Vdc
Collector–Base Breakdown Voltage ( $I_C = 10 \ \mu Adc, I_E = 0$ )	V(BR)CBO	60	-	Vdc
Emitter–Base Breakdown Voltage ( $I_E = 10 \ \mu Adc$ , $I_C = 0$ )	V(BR)EBO	6.0	-	Vdc
Base Cutoff Current (V <sub>CE</sub> = 30 Vdc, V <sub>EB</sub> = 3.0 Vdc)	I <sub>BL</sub>	_	50	nAdc
Collector Cutoff Current (V <sub>CE</sub> = 30 Vdc, V <sub>EB</sub> = 3.0 Vdc)	ICEX	_	50	nAdc

#### **ON CHARACTERISTICS**

DC Current Gain (Note 2.)		hFE			-
(I <sub>C</sub> = 0.1 mAdc, V <sub>CE</sub> = 1.0 Vdc)	2N3903		20	-	
	2N3904		40	-	
(I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 1.0 Vdc)	2N3903		35	-	
	2N3904		70	-	
(I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 1.0 Vdc)	2N3903		50	150	
	2N3904		100	300	
$(I_{C} = 50 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc})$	2N3903		30	-	
	2N3904		60	-	
$(I_{C} = 100 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc})$	2N3903		15	-	
	2N3904		30	-	
Collector–Emitter Saturation Voltage (Note 2.)		VCE(sat)			Vdc
$(I_{C} = 10 \text{ mAdc}, I_{B} = 1.0 \text{ mAdc})$		0 = (0 0.0)	-	0.2	
$(I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc})$			-	0.3	
Base–Emitter Saturation Voltage (Note 2.)		V <sub>BE(sat)</sub>			Vdc
(I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 1.0 mAdc)		, , ,	0.65	0.85	
$(I_C = 50 \text{ mAdc}, I_B = 5.0 \text{ mAdc})$			-	0.95	

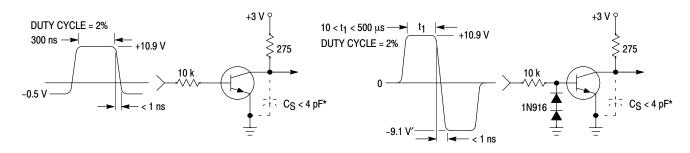
#### SMALL-SIGNAL CHARACTERISTICS

Current–Gain – Bandwidth Product ( $I_C = 10$ mAdc, $V_{CE} = 20$ Vdc, f = 100 MHz)	2N3903 2N3904	fT	250 300		MHz
Output Capacitance (V <sub>CB</sub> = 5.0 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	2110004	Cobo	-	4.0	pF
Input Capacitance (VEB = 0.5 Vdc, IC = 0, f = 1.0 MHz)		C <sub>ibo</sub>	-	8.0	pF
Input Impedance (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	2N3903 2N3904	h <sub>ie</sub>	1.0 1.0	8.0 10	kΩ
Voltage Feedback Ratio (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	2N3903 2N3904	h <sub>re</sub>	0.1 0.5	5.0 8.0	X 10 <sup>-4</sup>
Small–Signal Current Gain (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	2N3903 2N3904	h <sub>fe</sub>	50 100	200 400	-
Output Admittance ( $I_C$ = 1.0 mAdc, $V_{CE}$ = 10 Vdc, f = 1.0 kHz)		h <sub>oe</sub>	1.0	40	μmhos
Noise Figure (I <sub>C</sub> = 100 $\mu$ Adc, V <sub>CE</sub> = 5.0 Vdc, R <sub>S</sub> = 1.0 k $\Omega$ , f = 1.0 kHz)	2N3903 2N3904	NF		6.0 5.0	dB

#### SWITCHING CHARACTERISTICS

Delay Time	(V <sub>CC</sub> = 3.0 Vdc, V <sub>BE</sub> = 0.5 Vdc,		td	-	35	ns
Rise Time	I <sub>C</sub> = 10 mAdc, I <sub>B1</sub> = 1.0 mAdc)		tr	-	35	ns
Storage Time	$(V_{CC} = 3.0 \text{ Vdc}, I_{C} = 10 \text{ mAdc}, I_{B1} = I_{B2} = 1.0 \text{ mAdc})$	2N3903 2N3904	t <sub>S</sub>		175 200	ns
Fall Time			t <sub>f</sub>	-	50	ns

2. Pulse Test: Pulse Width  $\leq$  300 µs; Duty Cycle  $\leq$  2%.



\* Total shunt capacitance of test jig and connectors

Figure 1. Delay and Rise Time Equivalent Test Circuit Figure 2. Storage and Fall Time Equivalent Test Circuit

## **TYPICAL TRANSIENT CHARACTERISTICS**

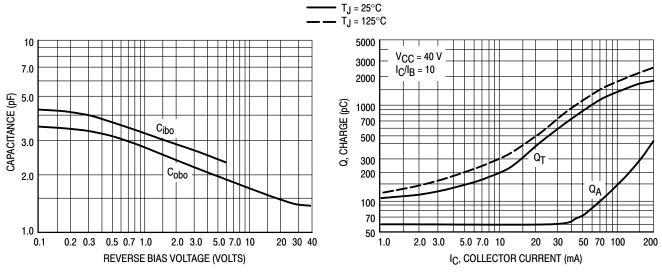
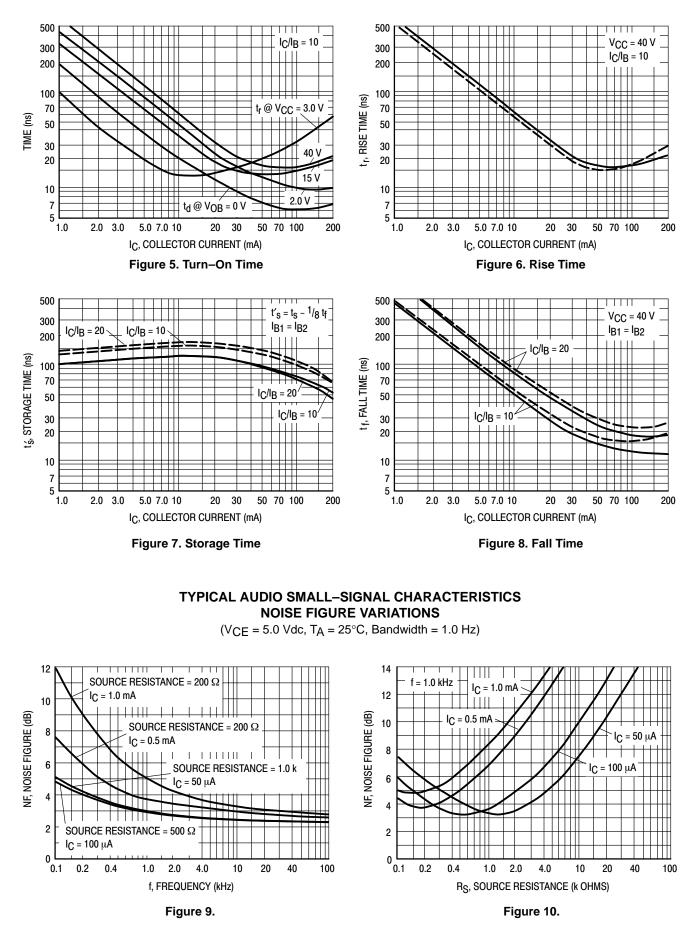


Figure 3. Capacitance

Figure 4. Charge Data



#### h PARAMETERS

(V<sub>CE</sub> = 10 Vdc, f = 1.0 kHz, T<sub>A</sub> = 25°C)

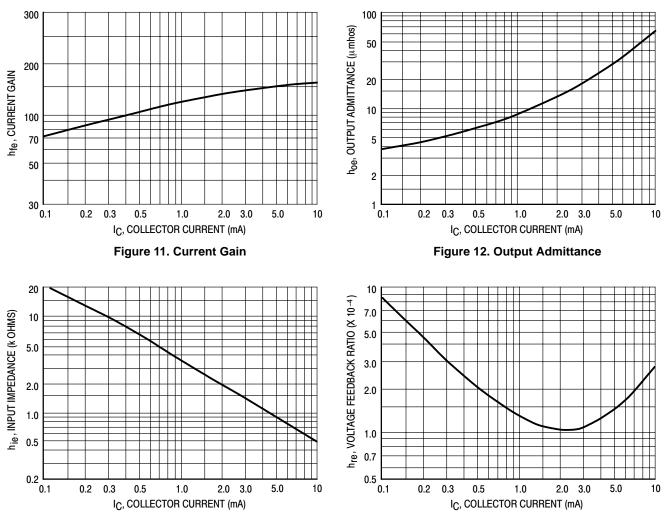
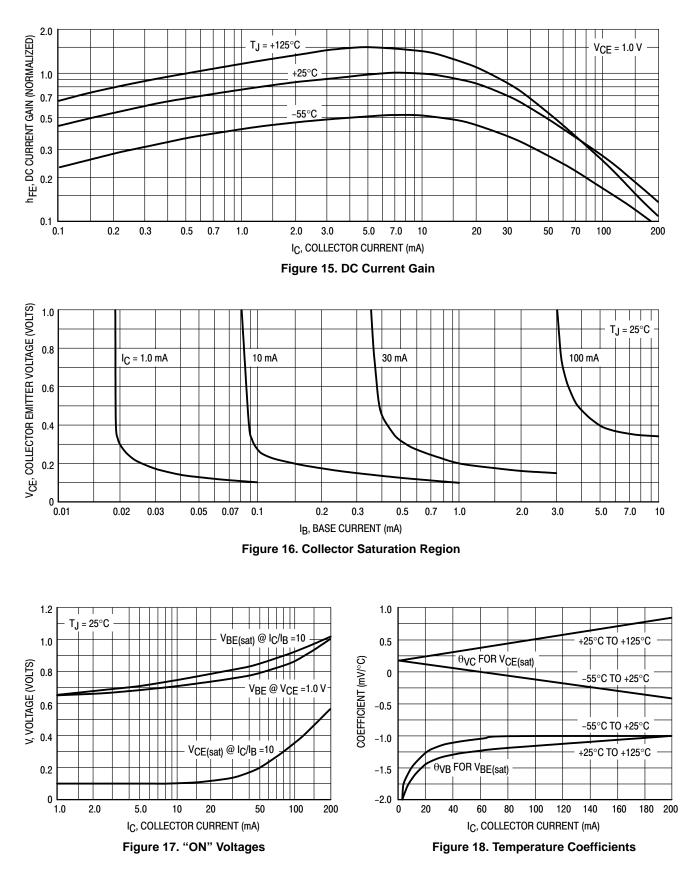


Figure 13. Input Impedance

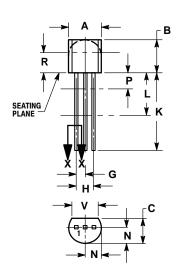
Figure 14. Voltage Feedback Ratio

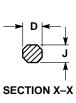
### TYPICAL STATIC CHARACTERISTICS



### PACKAGE DIMENSIONS

TO-92 TO-226AA CASE 29-11 **ISSUE AL** 





NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. CONTOUL OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED. 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
Κ	0.500		12.70	
L	0.250		6.35	
Ν	0.080	0.105	2.04	2.66
Ρ		0.100		2.54
R	0.115		2.93	
۷	0.135		3.43	

STYLE 1: PIN 1. EMITTER 2. BASE 3. COLLECTOR STYLE 14: PIN 1. EMITTER 2. COLLECTOR 3. BASE

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